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| SANYO | No.4756 | 2SC4923 |
| | NPN Triple Diffused Planar Silicon Transistor Very High-Definition CRT Display Horizontal Deflection Output Applications | |

Features

- High speed (t_f typ. = 100ns).
- High reliability (Adoption of HVP process).
- High breakdown voltage ($V_{CBO} = 1500V$).
- Adoption of MBIT process.

Absolute Maximum Ratings at $T_a = 25^\circ C$

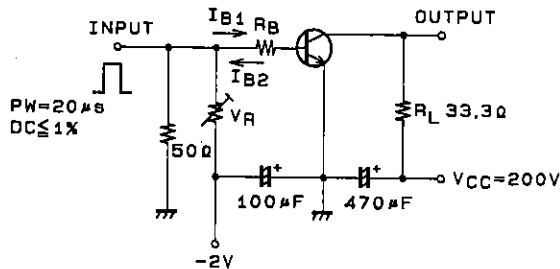
| | | | unit |
|------------------------------|-----------|-------------|------------|
| Collector-to-Base Voltage | V_{CBO} | 1500 | V |
| Collector-to-Emitter Voltage | V_{CEO} | 800 | V |
| Emitter-to-Base Voltage | V_{EBO} | 6 | V |
| Collector Current | I_C | 8 | A |
| Collector Current (Pulse) | I_{CP} | 25 | A |
| Collector Dissipation | P_C | 3.0 | W |
| | | 70 | W |
| Junction Temperature | T_j | 150 | $^\circ C$ |
| Storage Temperature | T_{stg} | -55 to +150 | $^\circ C$ |

$T_c = 25^\circ C$

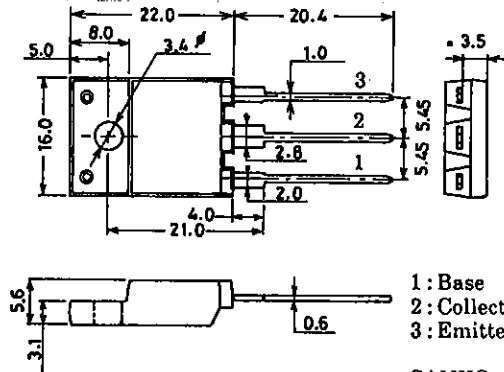
Electrical Characteristics at $T_a = 25^\circ C$

| | | | min | typ | max | unit |
|---------------------------|----------------|---|-----|-----|-----|---------|
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 800V, I_E = 0$ | | | 10 | μA |
| | I_{CES} | $V_{CE} = 1500V, R_{BE} = 0$ | | | 1.0 | mA |
| Collector Sustain Voltage | $V_{CEO(sus)}$ | $I_C = 100mA, I_B = 0$ | 800 | | | V |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = 4V, I_C = 0$ | | | 1.0 | mA |
| C-E Saturation Voltage | $V_{CE(sat)}$ | $I_C = 6A, I_B = 1.5A$ | | | 5 | V |
| B-E Saturation Voltage | $V_{BE(sat)}$ | $I_C = 6A, I_B = 1.5A$ | | | 1.5 | V |
| DC Current Gain | $h_{FE(1)}$ | $V_{CE} = 5V, I_C = 1A$ | 8 | | | |
| | $h_{FE(2)}$ | $V_{CE} = 5V, I_C = 6A$ | 4 | | 8 | |
| Storage Time | t_{stg} | $I_C = 6A, I_{B1} = 1.2A, I_{B2} = -2.4A$ | | | 3.0 | μs |
| Fall Time | t_f | $I_C = 6A, I_{B1} = 1.2A, I_{B2} = -2.4A$ | | 0.1 | 0.2 | μs |

Switching Time Test Circuit

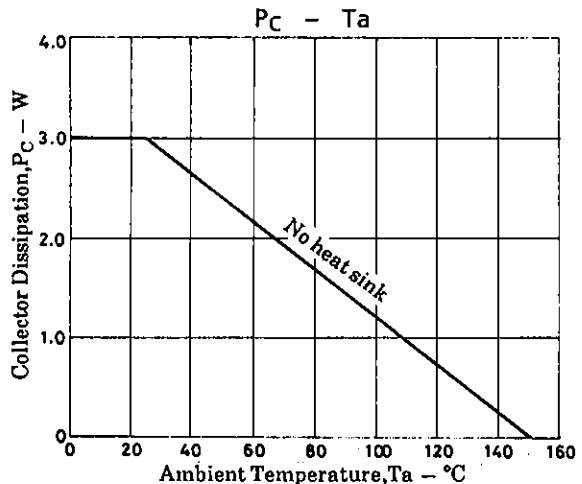
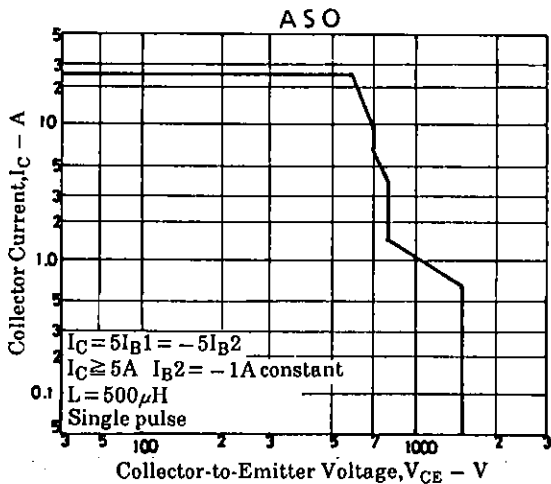
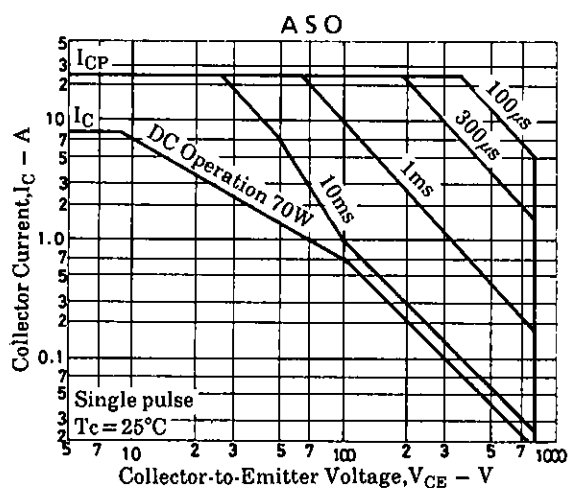
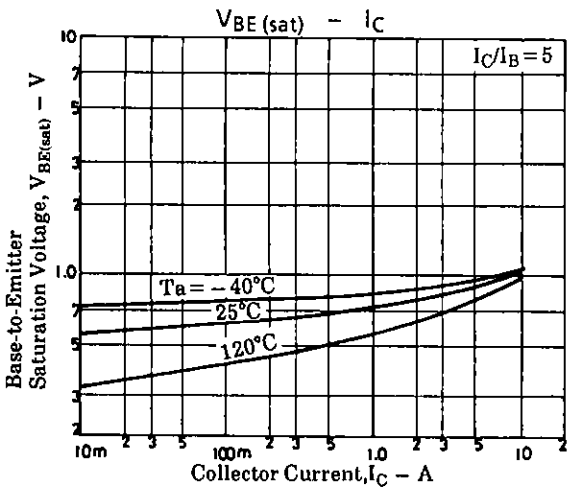
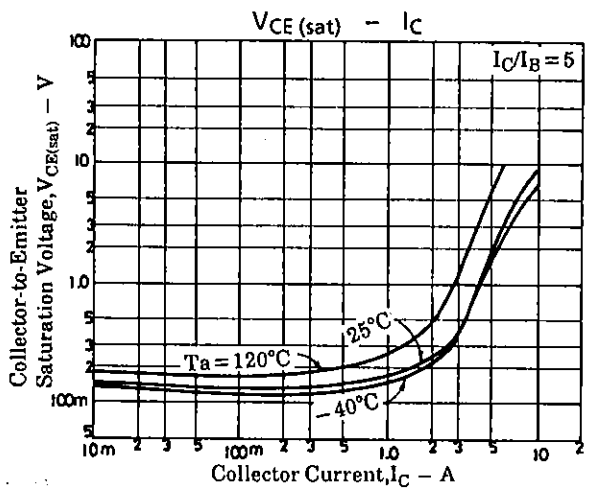
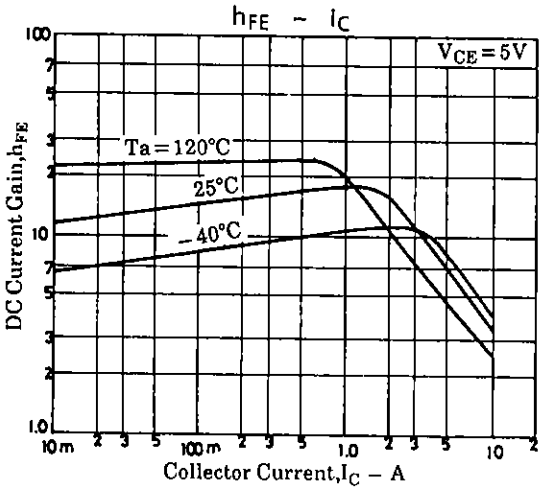
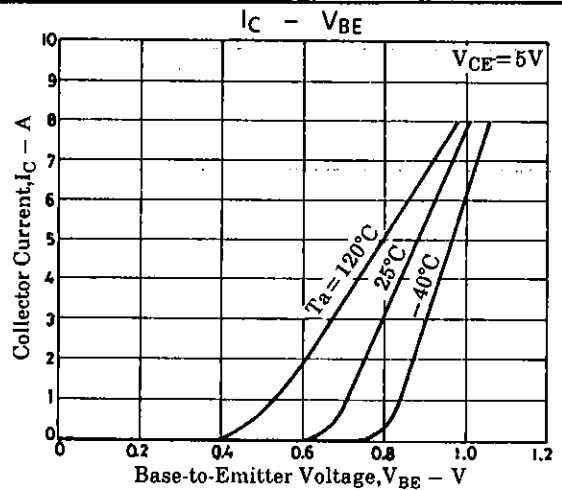
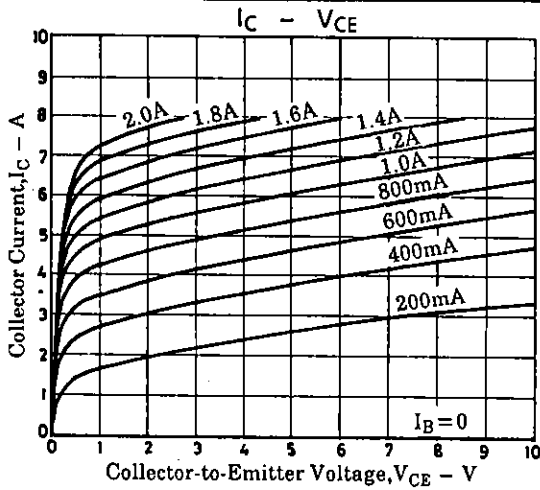


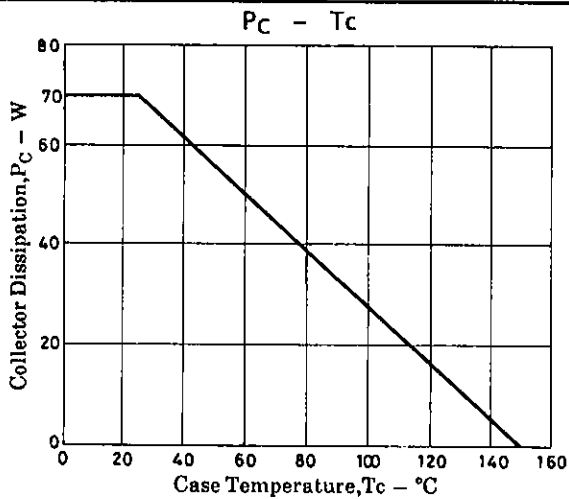
Package Dimensions 2039C (unit: mm)



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